

Marco Fanciulli

List of Publications by Year in descending order

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437
papers

12,332
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42291

92
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442
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442
docs citations

442
times ranked

12145
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 1 | Silicene field-effect transistors operating at room temperature. <i>Nature Nanotechnology</i> , 2015, 10, 227-231. | 15.6 | 1,429 |
| 2 | Nuclear HBx binds the HBV minichromosome and modifies the epigenetic regulation of cccDNA function. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2009, 106, 19975-19979. | 3.3 | 403 |
| 3 | Colloidal Synthesis of Double Perovskite Cs ₂ AgInCl ₆ and Mn-Doped Cs ₂ AgInCl ₆ Nanocrystals. <i>Journal of the American Chemical Society</i> , 2018, 140, 12989-12995. | 6.6 | 397 |
| 4 | Epitaxial growth of zinc blende and wurtzitic gallium nitride thin films on (001) silicon. <i>Applied Physics Letters</i> , 1991, 59, 944-946. | 1.5 | 367 |
| 5 | Two-Dimensional Si Nanosheets with Local Hexagonal Structure on a MoS ₂ Surface. <i>Advanced Materials</i> , 2014, 26, 2096-2101. | 11.1 | 311 |
| 6 | Local Electronic Properties of Corrugated Silicene Phases. <i>Advanced Materials</i> , 2012, 24, 5088-5093. | 11.1 | 278 |
| 7 | Evidence for graphite-like hexagonal AlN nanosheets epitaxially grown on single crystal Ag(111). <i>Applied Physics Letters</i> , 2013, 103, . | 1.5 | 251 |
| 8 | Towards Oxide Electronics: a Roadmap. <i>Applied Surface Science</i> , 2019, 482, 1-93. | 3.1 | 236 |
| 9 | Getting through the Nature of Silicene: An sp ² vs sp ³ Two-Dimensional Silicon Nanosheet. <i>Journal of Physical Chemistry C</i> , 2013, 117, 16719-16724. | 1.5 | 163 |
| 10 | Ozone-Based Atomic Layer Deposition of Alumina from TMA: Growth, Morphology, and Reaction Mechanism. <i>Chemistry of Materials</i> , 2006, 18, 3764-3773. | 3.2 | 161 |
| 11 | Hindering the Oxidation of Silicene with Non-Reactive Encapsulation. <i>Advanced Functional Materials</i> , 2013, 23, 4340-4344. | 7.8 | 161 |
| 12 | Analog Memristive Synapse in Spiking Networks Implementing Unsupervised Learning. <i>Frontiers in Neuroscience</i> , 2016, 10, 482. | 1.4 | 142 |
| 13 | Developmental factor IRF6 exhibits tumor suppressor activity in squamous cell carcinomas. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2011, 108, 13710-13715. | 3.3 | 141 |
| 14 | In situ chemical and structural investigations of the oxidation of Ge(001) substrates by atomic oxygen. <i>Applied Physics Letters</i> , 2006, 89, 083504. | 1.5 | 127 |
| 15 | Manipulation of two-dimensional arrays of Si nanocrystals embedded in thin SiO ₂ layers by low energy ion implantation. <i>Journal of Applied Physics</i> , 2004, 95, 5696-5702. | 1.1 | 115 |
| 16 | Glucose phosphorylation in tumor cells. Cloning, sequencing, and overexpression in active form of a full-length cDNA encoding a mitochondrial bindable form of hexokinase. <i>Journal of Biological Chemistry</i> , 1990, 265, 6481-6488. | 1.6 | 108 |
| 17 | Control of filament size and reduction of reset current below 10 ^{1/4} A in NiO resistance switching memories. <i>Solid-State Electronics</i> , 2011, 58, 42-47. | 0.8 | 103 |
| 18 | Atomic-layer deposition of Lu ₂ O ₃ . <i>Applied Physics Letters</i> , 2004, 85, 630-632. | 1.5 | 100 |

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|----|--|-----|-----------|
| 19 | Glucose phosphorylation in tumor cells. Cloning, sequencing, and overexpression in active form of a full-length cDNA encoding a mitochondrial bindable form of hexokinase. <i>Journal of Biological Chemistry</i> , 1990, 265, 6481-8. | 1.6 | 97 |
| 20 | Conductive-filament switching analysis and self-accelerated thermal dissolution model for reset in NiO-based RRAM. , 2007, , . | | 95 |
| 21 | Trap-Mediated Two-Step Sensitization of Manganese Dopants in Perovskite Nanocrystals. <i>ACS Energy Letters</i> , 2019, 4, 85-93. | 8.8 | 92 |
| 22 | Interface engineering for Ge metal-oxide semiconductor devices. <i>Thin Solid Films</i> , 2007, 515, 6337-6343. | 0.8 | 87 |
| 23 | Fabrication of GeO ₂ layers using a divalent Ge precursor. <i>Applied Physics Letters</i> , 2007, 90, 162115. | 1.5 | 84 |
| 24 | Combining grazing incidence X-ray diffraction and X-ray reflectivity for the evaluation of the structural evolution of HfO ₂ thin films with annealing. <i>Thin Solid Films</i> , 2004, 450, 134-137. | 0.8 | 76 |
| 25 | Conduction-electron spin resonance in zinc-blende GaN thin films. <i>Physical Review B</i> , 1993, 48, 15144-15147. | 1.1 | 74 |
| 26 | Combining high resolution and tensorial analysis in Raman stress measurements of silicon. <i>Journal of Applied Physics</i> , 2003, 94, 2729-2740. | 1.1 | 71 |
| 27 | Scaling analysis of submicrometer nickel-oxide-based resistive switching memory devices. <i>Journal of Applied Physics</i> , 2011, 109, . | 1.1 | 70 |
| 28 | HfO ₂ as gate dielectric on Ge: Interfaces and deposition techniques. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2006, 135, 256-260. | 1.7 | 68 |
| 29 | Phosphorus doping of ultra-small silicon nanocrystals. <i>Nanotechnology</i> , 2010, 21, 025602. | 1.3 | 68 |
| 30 | Silicon nanocrystal memory devices obtained by ultra-low-energy ion-beam synthesis. <i>Solid-State Electronics</i> , 2004, 48, 1511-1517. | 0.8 | 65 |
| 31 | Energy band alignment at TiO ₂ /Si interface with various interlayers. <i>Journal of Applied Physics</i> , 2008, 103, . | 1.1 | 63 |
| 32 | Bright Blue Emitting Cu-Doped Cs ₂ ZnCl ₄ Colloidal Nanocrystals. <i>Chemistry of Materials</i> , 2020, 32, 5897-5903. | 3.2 | 63 |
| 33 | Electrical and structural characteristics of yttrium oxide films deposited by rf-magnetron sputtering on n-Si. <i>Journal of Applied Physics</i> , 2003, 94, 318-325. | 1.1 | 60 |
| 34 | Energy-band diagram of metal/Lu ₂ O ₃ /silicon structures. <i>Applied Physics Letters</i> , 2004, 85, 5316-5318. | 1.5 | 60 |
| 35 | Vibrational and electrical properties of hexagonal La ₂ O ₃ films. <i>Applied Physics Letters</i> , 2007, 91, . | 1.5 | 59 |
| 36 | La ₂ Hf ₂ O ₇ high- κ gate dielectric grown directly on Si(001) by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2004, 85, 3205-3207. | 1.5 | 57 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 37 | The artificial zinc finger coding gene ϵ -Jazz TM binds the utrophin promoter and activates transcription. <i>Gene Therapy</i> , 2000, 7, 1076-1083. | 2.3 | 56 |
| 38 | Dielectric Properties of High- ϵ Oxides: Theory and Experiment for Lu ₂ O ₃ . <i>Physical Review Letters</i> , 2005, 94, 027602. | 2.9 | 56 |
| 39 | Defect-related local magnetism at dilute Fe atoms in ion-implanted ZnO. <i>Journal of Applied Physics</i> , 2007, 102, 113915. | 1.1 | 56 |
| 40 | Resistance switching in amorphous and crystalline binary oxides grown by electron beam evaporation and atomic layer deposition. <i>Microelectronic Engineering</i> , 2008, 85, 2414-2419. | 1.1 | 55 |
| 41 | Detection and characterization of silicon nanocrystals embedded in thin oxide layers. <i>Journal of Applied Physics</i> , 2004, 95, 257-262. | 1.1 | 53 |
| 42 | Engineering the electronic properties of silicene by tuning the composition of MoX ₂ and GaX (X = S, Se, Te) chalcogenide templates. <i>2D Materials</i> , 2014, 1, 011010. | 2.0 | 53 |
| 43 | Synaptic potentiation and depression in Al:HfO ₂ -based memristor. <i>Microelectronic Engineering</i> , 2015, 147, 41-44. | 1.1 | 53 |
| 44 | Conversion Electron Mössbauer Spectroscopy Study of Epitaxial FeSi ₂ Grown by Molecular Beam Epitaxy. <i>Physical Review Letters</i> , 1995, 75, 1642-1645. | 2.9 | 52 |
| 45 | Ru and RuO ₂ gate electrodes for advanced CMOS technology. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004, 109, 117-121. | 1.7 | 52 |
| 46 | Effects of the oxygen precursor on the electrical and structural properties of HfO ₂ films grown by atomic layer deposition on Ge. <i>Applied Physics Letters</i> , 2005, 87, 112904. | 1.5 | 52 |
| 47 | Spectroscopic ellipsometry study of thin NiO films grown on Si (100) by atomic layer deposition. <i>Applied Physics Letters</i> , 2008, 92, . | 1.5 | 52 |
| 48 | Vibrational properties of epitaxial silicene layers on (111) Ag. <i>Applied Surface Science</i> , 2014, 291, 113-117. | 3.1 | 49 |
| 49 | Experimental study of gradual/abrupt dynamics of HfO ₂ -based memristive devices. <i>Applied Physics Letters</i> , 2016, 109, . | 1.5 | 49 |
| 50 | Defects in diamond thin films. <i>Physical Review B</i> , 1993, 48, 14982-14988. | 1.1 | 48 |
| 51 | Chlorine mobility during annealing in N ₂ in ZrO ₂ and HfO ₂ films grown by atomic layer deposition. <i>Journal of Applied Physics</i> , 2002, 92, 7675-7677. | 1.1 | 48 |
| 52 | Nanoscale morphological and electrical homogeneity of HfO ₂ and ZrO ₂ thin films studied by conducting atomic-force microscopy. <i>Journal of Applied Physics</i> , 2005, 97, 074315. | 1.1 | 48 |
| 53 | High epitaxial quality Y ₂ O ₃ high- ϵ dielectric on vicinal Si(001) surfaces. <i>Applied Physics Letters</i> , 2002, 81, 3549-3551. | 1.5 | 47 |
| 54 | Thermal and Electrical Characterization of Materials for Phase-Change Memory Cells. <i>Journal of Chemical & Engineering Data</i> , 2009, 54, 1698-1701. | 1.0 | 47 |

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|----|--|-----|-----------|
| 55 | Conduction band offset of HfO ₂ on GaAs. Applied Physics Letters, 2007, 91, . | 1.5 | 46 |
| 56 | Charge state dependence of the diffusivity of interstitial Fe in silicon detected by Mössbauer spectroscopy. Applied Physics Letters, 2002, 80, 2657-2659. | 1.5 | 45 |
| 57 | Nanocrystals manufacturing by ultra-low-energy ion-beam-synthesis for non-volatile memory applications. Nuclear Instruments & Methods in Physics Research B, 2004, 216, 228-238. | 0.6 | 45 |
| 58 | Paramagnetism in Mn/Fe implanted ZnO. Applied Physics Letters, 2010, 97, . | 1.5 | 45 |
| 59 | Few electron limit of n-type metal oxide semiconductor single electron transistors. Nanotechnology, 2012, 23, 215204. | 1.3 | 44 |
| 60 | Tin-vacancy acceptor levels in electron-irradiated n-type silicon. Physical Review B, 2000, 62, 4535-4544. | 1.1 | 43 |
| 61 | X-Ray reflectivity and spectroscopic ellipsometry as metrology tools for the characterization of interfacial layers in high- κ materials. Thin Solid Films, 2004, 450, 124-127. | 0.8 | 43 |
| 62 | Ab initio study of magnetic interaction of Fe doped ZnO with intrinsic vacancies. Applied Physics Letters, 2007, 90, 212510. | 1.5 | 43 |
| 63 | Cubic-to-monoclinic phase transition during the epitaxial growth of crystalline Gd ₂ O ₃ films on Ge(001) substrates. Applied Physics Letters, 2007, 90, 193511. | 1.5 | 41 |
| 64 | Evidence of dangling bond electrical activity at the Ge/oxide interface. Applied Physics Letters, 2008, 93, . | 1.5 | 41 |
| 65 | Engineering the Growth of MoS ₂ via Atomic Layer Deposition of Molybdenum Oxide Film Precursor. Advanced Electronic Materials, 2016, 2, 1600330. | 2.6 | 41 |
| 66 | Luminescence from FeSi_2 precipitates in Si. I. Morphology and epitaxial relationship. Physical Review B, 2002, 66, . | 1.1 | 40 |
| 67 | Energy band alignment of HfO ₂ on Ge. Journal of Applied Physics, 2006, 100, 093718. | 1.1 | 40 |
| 68 | Computation of the Stark effect in P impurity states in silicon. Physical Review B, 2006, 74, . | 1.1 | 40 |
| 69 | Atomic Layer Deposition of NiO Films on Si(100) Using Cyclopentadienyl-Type Compounds and Ozone as Precursors. Journal of the Electrochemical Society, 2008, 155, H807. | 1.3 | 40 |
| 70 | Oxidation and reduction kinetics of eutectic SnPb, InSn, and AuSn: a knowledge base for fluxless solder bonding applications. IEEE Transactions on Components, Packaging and Manufacturing Technology Part C Manufacturing, 1998, 21, 134-141. | 0.4 | 39 |
| 71 | Compact silicon double and triple dots realized with only two gates. Applied Physics Letters, 2009, 95, . | 1.5 | 38 |
| 72 | Atomic layer deposition of rare-earth-based binary and ternary oxides for microelectronic applications. Semiconductor Science and Technology, 2012, 27, 074013. | 1.0 | 38 |

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|----|---|-----|-----------|
| 73 | Atomic layer deposition of $\text{La}_x\text{Zr}_{1-x}\text{O}_2$ ($x=0.25$) high-k dielectrics for advanced gate stacks. Applied Physics Letters, 2009, 94, . | 1.5 | 37 |
| 74 | Dielectric properties of $\text{Er}^{1/4}$ -doped HfO_2 ($\text{Er}^{1/4} 15\%$) grown by atomic layer deposition for high- I^{on} gate stacks. Applied Physics Letters, 2010, 96, . | 1.5 | 37 |
| 75 | Conversion electron Mössbauer spectroscopy study of iron silicide films grown by MBE;. Physica Scripta, 1994, T54, 16-19. | 1.2 | 36 |
| 76 | Structural and electrical characterization of ALCVD ZrO_2 thin films on silicon. Journal of Non-Crystalline Solids, 2002, 303, 29-34. | 1.5 | 35 |
| 77 | Effective Hamiltonian for the hybrid double quantum dot qubit. Quantum Information Processing, 2014, 13, 1155-1173. | 1.0 | 35 |
| 78 | Electroporation Enhances Bleomycin Efficacy in Cats with Periocular Carcinoma and Advanced Squamous Cell Carcinoma of the Head. Journal of Veterinary Internal Medicine, 2015, 29, 1368-1375. | 0.6 | 35 |
| 79 | Electronic Structures of Semiconductors under Pressure. Physica Status Solidi (B): Basic Research, 1996, 198, 23-34. | 0.7 | 34 |
| 80 | Microscopic environment of Fe in epitaxially stabilized c^{at} -FeSi. Physical Review B, 1999, 59, 3675-3687. | 1.1 | 34 |
| 81 | Silicon self-diffusivity measurement in thermal SiO_2 by $^{30}\text{Si}/^{28}\text{Si}$ isotopic exchange. Journal of Applied Physics, 2003, 94, 2136-2138. | 1.1 | 34 |
| 82 | Metal Organic Chemical Vapor Deposition of Phase Change $\text{Ge}_{1-x}\text{Sb}_x\text{Te}_4$ Nanowires. Nano Letters, 2012, 12, 1509-1515. | 4.5 | 34 |
| 83 | Exploring the morphological and electronic properties of silicene superstructures. Applied Surface Science, 2014, 291, 109-112. | 3.1 | 34 |
| 84 | Study of defects in wide band gap semiconductors by electron paramagnetic resonance. Physica B: Condensed Matter, 1993, 185, 228-233. | 1.3 | 33 |
| 85 | Infrared spectroscopy and X-ray diffraction studies on the crystallographic evolution of La_2O_3 films upon annealing. Microelectronic Engineering, 2008, 85, 2411-2413. | 1.1 | 33 |
| 86 | CVD synthesis of polycrystalline magnetite thin films: structural, magnetic and magnetotransport properties. Journal Physics D: Applied Physics, 2010, 43, 065002. | 1.3 | 33 |
| 87 | Low-temperature atomic layer deposition of MgO thin films on Si. Journal Physics D: Applied Physics, 2013, 46, 485304. | 1.3 | 33 |
| 88 | Rhein inhibits glucose uptake in Ehrlich ascites tumor cells by alteration of membrane-associated functions. Anti-Cancer Drugs, 1993, 4, 407-414. | 0.7 | 32 |
| 89 | Conversion electron Mössbauer spectroscopy study of iron disilicide films grown by MBE. Thin Solid Films, 1996, 275, 8-11. | 0.8 | 32 |
| 90 | Thin MnO and NiO films grown using atomic layer deposition from ethylcyclopentadienyl type of precursors. Journal of Crystal Growth, 2008, 310, 5464-5468. | 0.7 | 32 |

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| 91 | HfO ₂ -based memristors for neuromorphic applications. , 2016, , . | | 32 |
| 92 | Hardness, elastic modulus, and wear resistance of hafnium oxide-based films grown by atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, . | 0.9 | 32 |
| 93 | Trends of structural and electrical properties in atomic layer deposited HfO ₂ films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 109, 11-16. | 1.7 | 31 |
| 94 | Band alignment at the La ₂ Hf ₂ O ₇ /(001)Si interface. Applied Physics Letters, 2006, 88, 202903. | 1.5 | 31 |
| 95 | Thermally induced permittivity enhancement in La-doped ZrO ₂ grown by atomic layer deposition on Ge(100). Applied Physics Letters, 2009, 95, 122902. | 1.5 | 31 |
| 96 | Influence of the oxidizing species on the Ge dangling bonds at the (100)Ge/GeO ₂ interface. Applied Physics Letters, 2010, 96, . | 1.5 | 31 |
| 97 | Fe/BaTiO ₃ interface: Band alignment and chemical properties. Applied Physics Letters, 2011, 99, 182905. | 1.5 | 31 |
| 98 | O ₃ -based atomic layer deposition of hexagonal La ₂ O ₃ films on Si(100) and Ge(100) substrates. Journal of Applied Physics, 2010, 108, 084108. | 1.1 | 30 |
| 99 | Adiabatic charge control in a single donor atom transistor. Applied Physics Letters, 2011, 98, 053109. | 1.5 | 30 |
| 100 | ^{69,71} GaNMR spectra and relaxation in wurtzite GaN. Physical Review B, 2003, 67, . | 1.1 | 29 |
| 101 | Raman spectroscopy of strain in subwavelength microelectronic devices. Applied Physics Letters, 2005, 87, 111913. | 1.5 | 29 |
| 102 | Chemical/Structural Nanocharacterization and Electrical Properties of ALD-Grown La ₂ O ₃ /Si Interfaces for Advanced Gate Stacks. Journal of the Electrochemical Society, 2009, 156, H1. | 1.3 | 29 |
| 103 | Microwave-assisted transport in a single-donor silicon quantum dot. Physical Review B, 2009, 80, . | 1.1 | 29 |
| 104 | Electric-field gradient at the Fe nucleus in μ -FeSi. Physical Review B, 1996, 54, 15985-15990. | 1.1 | 28 |
| 105 | Raman spectroscopy for a micrometric and tensorial analysis of stress in silicon. Applied Physics Letters, 2002, 81, 3377-3379. | 1.5 | 28 |
| 106 | X-ray photoelectron spectroscopy study of energy-band alignments of Lu ₂ O ₃ on Ge. Surface and Interface Analysis, 2006, 38, 494-497. | 0.8 | 28 |
| 107 | Formation and stability of germanium oxide induced by atomic oxygen exposure. Materials Science in Semiconductor Processing, 2006, 9, 673-678. | 1.9 | 28 |
| 108 | Electron Confinement at the Si/MoS ₂ Heterosheet Interface. Advanced Materials Interfaces, 2016, 3, 1500619. | 1.9 | 28 |

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|-----|--|-----|-----------|
| 109 | Strong confinement-induced engineering of the g factor and lifetime of conduction electron spins in Ge quantum wells. <i>Nature Communications</i> , 2016, 7, 13886. | 5.8 | 28 |
| 110 | Divacancy-tin complexes in electron-irradiated silicon studied by EPR. <i>Physical Review B</i> , 2000, 61, 2657-2671. | 1.1 | 27 |
| 111 | Effects of growth temperature on the properties of atomic layer deposition grown ZrO ₂ films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2003, 21, 1359-1365. | 0.9 | 27 |
| 112 | Investigation of point defects at the high-k oxides/Si(100) interface by electrically detected magnetic resonance. <i>Journal of Non-Crystalline Solids</i> , 2003, 322, 168-173. | 1.5 | 26 |
| 113 | Coherent tunneling by adiabatic passage of an exchange-only spin qubit in a double quantum dot chain. <i>Physical Review B</i> , 2015, 91, . | 1.1 | 26 |
| 114 | The electronic configuration of substitutional Fe in silicon. <i>Physica B: Condensed Matter</i> , 1999, 273-274, 363-366. | 1.3 | 25 |
| 115 | Quantitative depth profiling at silicon/silicon oxide interfaces by means of Cs ⁺ sputtering in negative mode by ToF-SIMS: a full spectrum approach. <i>Applied Surface Science</i> , 2003, 203-204, 52-55. | 3.1 | 25 |
| 116 | Local structure of Sn implanted in thin SiO ₂ films. <i>Physical Review B</i> , 2003, 68, . | 1.1 | 25 |
| 117 | Time of flight secondary ion mass spectrometry study of silicon nanoclusters embedded in thin silicon oxide layers. <i>Applied Physics Letters</i> , 2003, 82, 121-123. | 1.5 | 25 |
| 118 | [(Me ₃ Si) ₂ N] ₃ Lu: Molecular Structure and Use as Lu and Si Source for Atomic Layer Deposition of Lu Silicate Films. <i>Zeitschrift Fur Anorganische Und Allgemeine Chemie</i> , 2007, 633, 2097-2103. | 0.6 | 25 |
| 119 | Ge-based interface passivation for atomic layer deposited La-doped ZrO ₂ on III-V compound (GaAs, In _{0.15} Ga _{0.85} As) substrates. <i>Applied Physics Letters</i> , 2009, 95, 023507. | 1.5 | 25 |
| 120 | Charge dynamics of a single donor coupled to a few-electron quantum dot in silicon. <i>Applied Physics Letters</i> , 2012, 100, . | 1.5 | 25 |
| 121 | Phase Stabilization of Al:HfO ₂ Grown on In _x Ga _{1-x} As Substrates (x = 0, 0.15, 0.53) via Trimethylaluminum-Based Atomic Layer Deposition. <i>ACS Applied Materials & Interfaces</i> , 2014, 6, 3455-3461. | 4.0 | 25 |
| 122 | Universal set of quantum gates for double-dot exchange-only spin qubits with intradot coupling. <i>Journal of Physics A: Mathematical and Theoretical</i> , 2015, 48, 065304. | 0.7 | 25 |
| 123 | Study of defects in diamond films with electron paramagnetic resonance measurements. <i>Diamond and Related Materials</i> , 1992, 1, 773-775. | 1.8 | 24 |
| 124 | Raman stress maps from finite-element models of silicon structures. <i>Journal of Applied Physics</i> , 2006, 100, 033516. | 1.1 | 24 |
| 125 | Study of the interfaces in resistive switching NiO thin films deposited by both ALD and e-beam coupled with different electrodes (Si, Ni, Pt, W, TiN). <i>Microelectronic Engineering</i> , 2008, 85, 2425-2429. | 1.1 | 24 |
| 126 | A random number generator based on the logit transform of the logistic variable. <i>Computers in Physics</i> , 1992, 6, 630. | 0.6 | 23 |

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|-----|---|-----|-----------|
| 127 | Electronic Structure of Defect Centers P1, P2, and P4 in P-Doped SiO ₂ . Journal of Physical Chemistry B, 2001, 105, 6097-6102. | 1.2 | 23 |
| 128 | CMOS fully compatible microwave detector based on MOSFET operating in resistive regime. IEEE Microwave and Wireless Components Letters, 2005, 15, 445-447. | 2.0 | 23 |
| 129 | X-ray absorption study of the growth of Y ₂ O ₃ on Si(001). Physical Review B, 2005, 71, . | 1.1 | 23 |
| 130 | The fabrication of tunable nanoporous oxide surfaces by block copolymer lithography and atomic layer deposition. Nanotechnology, 2011, 22, 335303. | 1.3 | 23 |
| 131 | Theoretical aspects of graphene-like group IV semiconductors. Applied Surface Science, 2014, 291, 98-103. | 3.1 | 23 |
| 132 | Nucleation and temperature-driven phase transitions of silicene superstructures on Ag(111). Journal of Physics Condensed Matter, 2015, 27, 255005. | 0.7 | 23 |
| 133 | ⁵⁷ Fe Mössbauer study of radiation damage in ion-implanted Si, SiGe and SiSn. Nuclear Instruments & Methods in Physics Research B, 2002, 186, 55-60. | 0.6 | 22 |
| 134 | X-ray absorption spectroscopy study of Yb ₂ O ₃ and Lu ₂ O ₃ thin films deposited on Si(100) by atomic layer deposition. Nuclear Instruments & Methods in Physics Research B, 2006, 246, 90-95. | 0.6 | 22 |
| 135 | Germanium diffusion during HfO ₂ growth on Ge by molecular beam epitaxy. Applied Physics Letters, 2006, 89, 122906. | 1.5 | 22 |
| 136 | The magnetic interaction of Fe doped ZnO with intrinsic defects: A first principles study. Physica B: Condensed Matter, 2007, 401-402, 451-453. | 1.3 | 22 |
| 137 | Microwave irradiation effects on random telegraph signal in a MOSFET. Physics Letters, Section A: General, Atomic and Solid State Physics, 2007, 370, 491-493. | 0.9 | 22 |
| 138 | Structural and electrical properties of atomic layer deposited Al-doped ZrO ₂ films and of the interface with TaN electrode. Journal of Applied Physics, 2012, 112, . | 1.1 | 22 |
| 139 | Chemical vapor deposition growth of Fe ₃ O ₄ thin films and Fe/Fe ₃ O ₄ bi-layers for their integration in magnetic tunnel junctions. Thin Solid Films, 2012, 520, 4617-4621. | 0.8 | 22 |
| 140 | Mössbauer investigation of silicide phases at the reactive Fe/Si interface. Applied Surface Science, 1998, 123-124, 207-212. | 3.1 | 21 |
| 141 | Mössbauer spectroscopy on Fe impurities in germanium. Physica B: Condensed Matter, 2003, 340-342, 537-540. | 1.3 | 21 |
| 142 | Electron spin-echo relaxation and envelope modulation of shallow phosphorus donors in silicon. Physical Review B, 2005, 72, . | 1.1 | 21 |
| 143 | Au-catalyzed self assembly of GeTe nanowires by MOCVD. Journal of Crystal Growth, 2011, 315, 152-156. | 0.7 | 21 |
| 144 | Magnetic Transitions and Energy Transfer Processes in Sb-Based Zero-Dimensional Metal Halide Nanocrystals Doped with Manganese. ACS Energy Letters, 2022, 7, 1566-1573. | 8.8 | 21 |

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|-----|---|-----|-----------|
| 145 | The electronic configuration of Fe in. Journal of Physics Condensed Matter, 1997, 9, 1619-1630. | 0.7 | 20 |
| 146 | Mössbauer Spectroscopy of Fe in Silicon with the Novel Laser-Ionized $^{57}\text{Mn}^{+}$ Ion Beam at Isolde. Materials Science Forum, 1997, 258-263, 437-442. | 0.3 | 20 |
| 147 | Diffusion Reaction of Oxygen in HfO ₂ /SiO ₂ /Si Stacks. Journal of Physical Chemistry B, 2006, 110, 14905-14910. | 1.2 | 20 |
| 148 | The structure of charge-compensated Fe ³⁺ ions in ZnO. Physica B: Condensed Matter, 2007, 401-402, 382-385. | 1.3 | 20 |
| 149 | Atomic Layer Deposition of Magnetic Thin Films. Acta Physica Polonica A, 2007, 112, 1271-1280. | 0.2 | 20 |
| 150 | Binding Properties of the Artificial Zinc Fingers Coding Gene Sint1. Biochemical and Biophysical Research Communications, 1998, 253, 686-692. | 1.0 | 19 |
| 151 | Carbon-tin defects in silicon. Physical Review B, 2001, 64, . | 1.1 | 19 |
| 152 | Creation and annealing of defect structures in silicon-based semiconductors during and after implantations at 77 K. Nuclear Instruments & Methods in Physics Research B, 2003, 206, 90-94. | 0.6 | 19 |
| 153 | Structure evolution of atomic layer deposition grown ZrO ₂ films by deep-ultra-violet Raman and far-infrared spectroscopies. Journal of Non-Crystalline Solids, 2003, 322, 105-110. | 1.5 | 19 |
| 154 | Coordination of boron and phosphorous in borophosphosilicate glasses. Applied Physics Letters, 2003, 83, 4312-4314. | 1.5 | 19 |
| 155 | Growth study of GexSbyTez deposited by MOCVD under nitrogen for non-volatile memory applications. Journal of Crystal Growth, 2008, 310, 5053-5057. | 0.7 | 19 |
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